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ABSTRACT OF THE DISCLOSURE

STRUCTURE OF P-ELECTRODE AT THE LIGHT-EMERGING SIDE OF LIGHT-EMITTING DIODE

A structure of a p-electrode formed at the light-emerging side of an LED that comprises (a) an n-type semiconductor substrate, (b) an n-type cladding layer, an active layer, a p-type cladding layer, and a p-type contact layer formed on the substrate in this order, and (c) an n-electrode formed on the back face of the substrate. The structure of the p-electrode comprises a mesh-shaped semi-transparent thin-film metal electrode for diffusing electric current formed on the p-type contact layer and a bonding electrode for wire bonding. The metal electrode comprises a covering portion having a transmittance of at least 10% and an opening portion having an opening ratio of at least 20%. The bonding electrode is formed at the periphery of the p-type contact layer and is bonded directly to the mesh-shaped semi-transparent thin-film metal electrode. This structure can increase the intensity of the output light emerging from the p-side.

Figure 2.



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